

Discrete POWER & Signal **Technologies**

PN4250A



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 68. See PN200 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	60	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5.0	V
lc	Collector Current - Continuous	500	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		PN4250A	
P_D	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
R ₀ JC	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

¹⁾ These ratings are based on a maximum junction temperature of 150 degrees C.

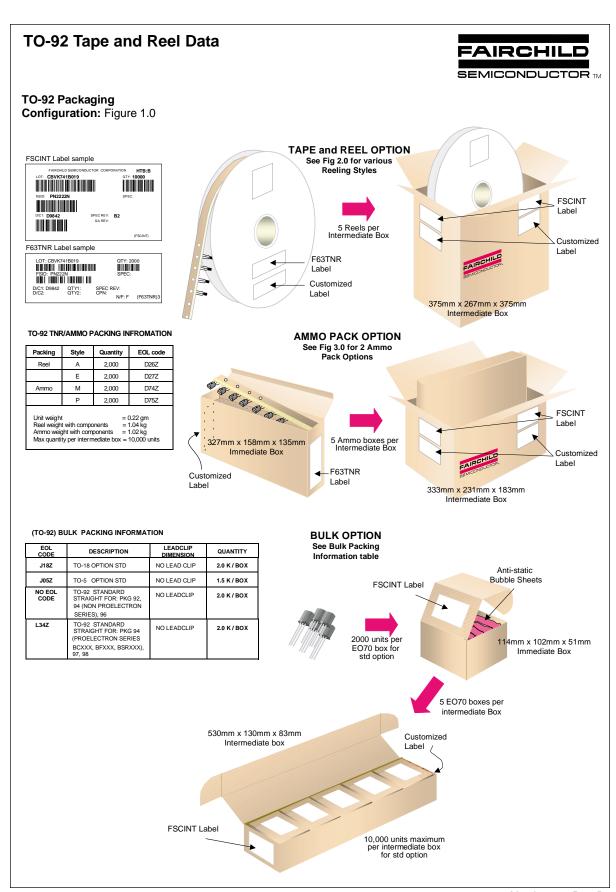
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

^{© 1997} Fairchild Semiconductor Corporation

PNP General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 5.0 \text{ mA}, I_B = 0$	60		V
V _{(BR)CES}	Collector-Emitter Breakdown Voltage*	$I_C = 10 \mu A, I_B = 0$	60		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	5.0		V
Ісво	Collector-Cutoff Current	V _{CB} = 50 V, I _E = 0		10	nA
I _{EBO}	Emitter-Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_{C} = 0$		20	nA
	RACTERISTICS*	Vc= = 5.0 V. lc = 100 uA	250	700	
h _{FE}		$V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$ $I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA}$	250	700 0.25	V
h _{FE} V _{CE(sat)}	DC Current Gain Collector-Emitter Saturation Voltage GIGNAL CHARACTERISTICS Output Capacitance	$I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$		0.25	V
h _{FE} V _{CE(sat)} SMALL S C _{ob}	DC Current Gain Collector-Emitter Saturation Voltage IGNAL CHARACTERISTICS Output Capacitance Small-signal Current Gain	$I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$ $V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA},$	250	0.25 6.0 800	pF
h _{FE} V _{CE(sat)}	DC Current Gain Collector-Emitter Saturation Voltage GNAL CHARACTERISTICS Output Capacitance Small-signal Current Gain Input Impedance	$I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$	250 6.0	6.0 800 20	pF kΩ
h _{FE} VCE(sat) SMALL S Cob hfe hie hoe	DC Current Gain Collector-Emitter Saturation Voltage GIGNAL CHARACTERISTICS Output Capacitance Small-signal Current Gain Input Impedance Output Admittance	$I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$ $V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA},$	250	6.0 800 20 50	pF kΩ μmhos
h _{FE} V _{CE(sat)} SMALL S C _{ob} h _{fe} h _{ie}	DC Current Gain Collector-Emitter Saturation Voltage GNAL CHARACTERISTICS Output Capacitance Small-signal Current Gain Input Impedance	$I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$ $V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA},$	250 6.0	6.0 800 20	pF kΩ

^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

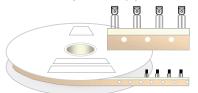


©2001 Fairchild Semiconductor Corporation

TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)



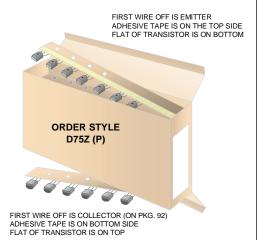
Style "A", D26Z, D70Z (s/h)

Machine Option "E" (J)

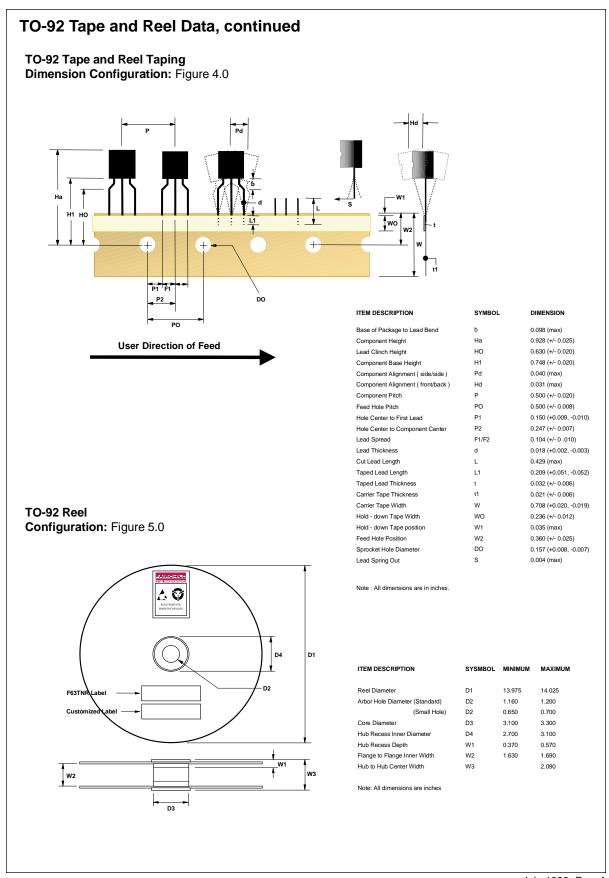
Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0





September 1999, Rev. B



TO-92 Package Dimensions FAIRCHILD SEMICONDUCTOR TM TO-92 (FS PKG Code 92, 94, 96) Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters] Part Weight per unit (gram): 0.1977 0.185 4.70 0.170 4.32 TO-92 (92,94,96) 94 96 B F В В В D D 2 В S С G Ε Ø0.060 [Ø1.52] G В S С G 0.010 [0.254] DEEP 5.0°TYP.

©2000 Fairchild Semiconductor International

0.095 0.084 2.13

January 2000, Rev. B

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

 $ACEx^{TM}$ FASTr™ PowerTrench® SyncFET™ QFET™ TinyLogic™ Bottomless™ GlobalOptoisolator™ QSTM UHC™ CoolFET™ GTO™ **VCX**TM $CROSSVOLT^{TM}$ QT Optoelectronics™ HiSeC™

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

Rev. G